

GL4403

PNP EPITAXIAL PLANAR TRANSISTOR

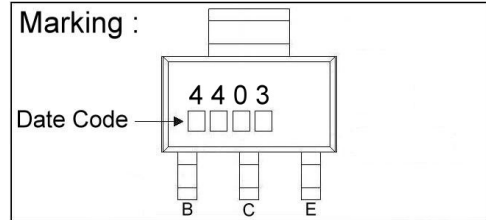
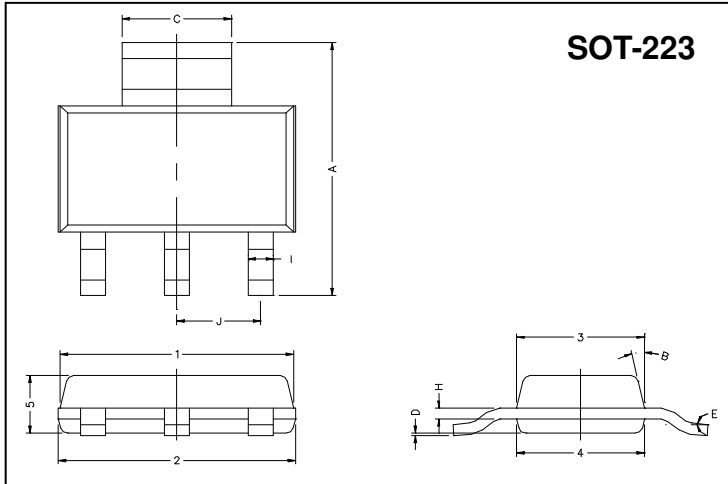
Description

The GL4403 is designed for general purpose switching and amplifier applications.

Features

- Complementary to GL4401
- High Power Dissipation: 1500mW at 25°C
- High DC Current Gain: 100-300 at 150mA

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13° TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage at Ta=25°C	VCBO	-40	V
Collector to Emitter Voltage at Ta=25°C	VCEO	-40	V
Emitter to Base Voltage at Ta=25°C	VEBO	-5	V
Collector Current at Ta=25°C	IC	-600	mA
Total Power Dissipation at Ta=25°C	PD	1.5	W

Characteristics at Ta = 25°C

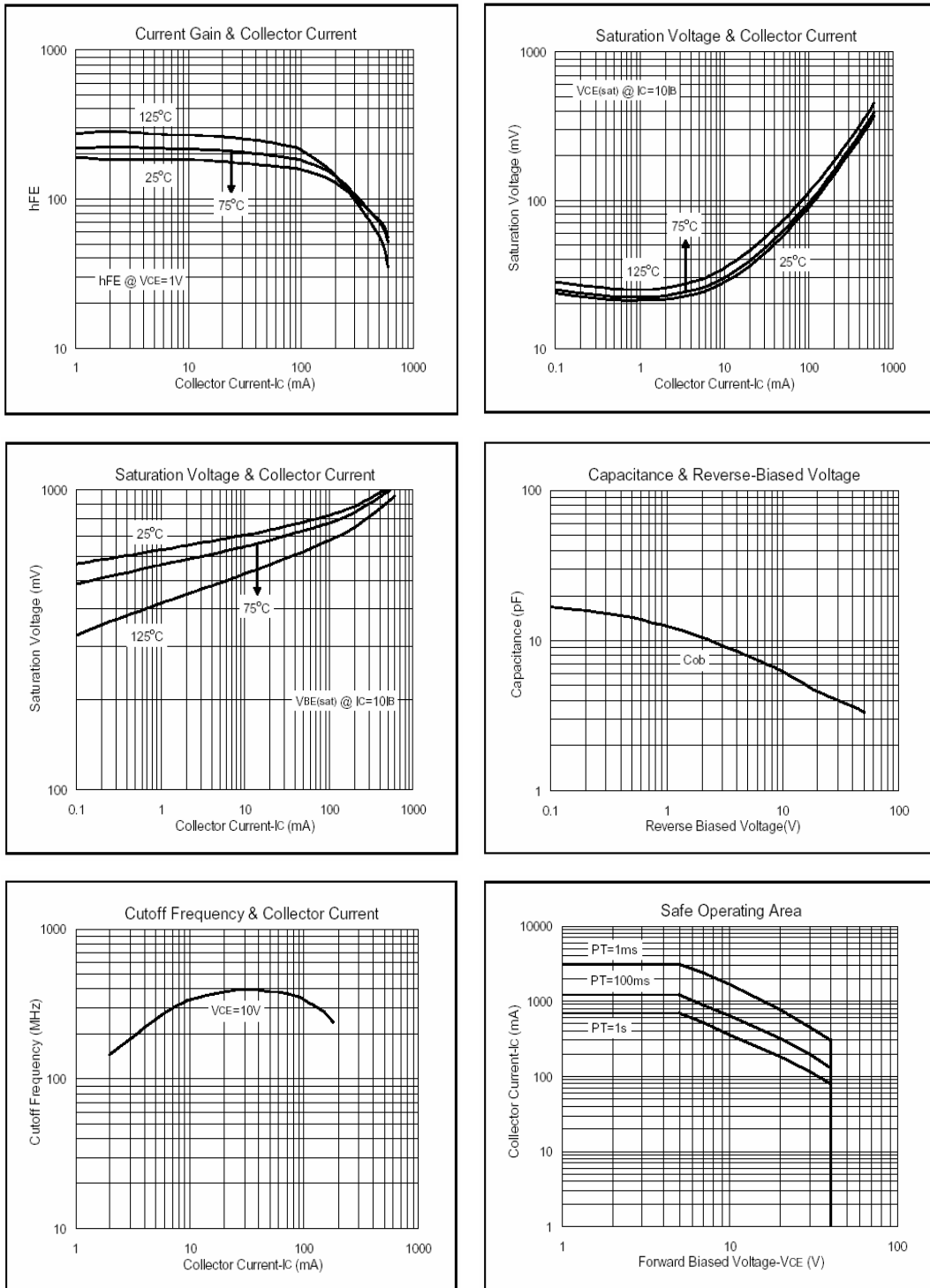
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-40	-	-	V	IC=-100uA
BVCEO	-40	-	-	V	IC=-1mA
BVEBO	-5	-	-	V	IE=-10uA
ICEX	-	-	-100	nA	VCE=-35V, VBE=-0.4V
*VCE(sat)1	-	-	-400	mV	IC=-150mA, IB=-15mA
*VCE(sat)2	-	-	-750	mV	IC=-500mA, IB=-50mA
*VBE(sat)1	-750	-	-950	mV	IC=-150mA, IB=-15mA
*VBE(sat)2	-	-	-1.3	V	IC=-500mA, IB=-50mA
*hFE1	30	-	-		VCE=-1V, IC=-0.1mA
*hFE2	60	-	-		VCE=-1V, IC=-1mA
*hFE3	100	-	-		VCE=-1V, IC=-10mA
*hFE4	100	-	300		VCE=-2V, IC=-150mA
*hFE5	20	-	-		VCE=-2V, IC=-500mA
fT	200	-	-	MHz	VCE=-10V, IC=-20mA, f=100MHz
Cob	-	-	8.5	pF	VCE=-10V, f=1MHz

Classification Of hFE4

Rank	A	B
Range	100-210	190-300

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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